REMARKS

The Official Action mailed October 5, 2005 has been received and its contents carefully noted. This response is filed within three months of the mailing date of the Official Action and therefore is believed to be timely without extension of time.

The Applicants note with appreciation the consideration of the Information Disclosure Statements filed on December 1, 2003; February 25, 2004; August 10, 2004; August 30, 2004 and May 2, 2005.

Claims 1-18 were pending in the present application prior to the above amendment, of which claims 1, 4, 6, 8 and 13 are independent. The Applicants note with appreciation the indication of the allowability of dependent claim 3 (pages 3-4, Paper No. 100305) and the allowance of claims 4-7 (page 4, <u>Id.</u>). Claim 3 has been canceled, and claims independent claims 1, 8 and 13 have been amended to incorporate allowable subject matter. Accordingly, claims 1, 2 and 4-18 are now pending in the present application, of which claims 1, 4, 6, 8 and 13 are independent. For the reasons set forth in detail below, all claims are believed to be in condition for allowance. Favorable reconsideration is requested.

Paragraph 2 of the Official Action rejects claims 8-18 as obvious based on U.S. Patent No. 4,434,036 to Hoerschelmann et al. Paragraph 3 of the Official Action rejects claims 1 and 2 as obvious based on the combination of Hoerschelmann and U.S. Patent No. 4,465,529 to Arima et al. The Applicants respectfully submit that an anticipation or obviousness rejection cannot be maintained against the independent claims of the present application, as amended.

The Official Action states that "Claim 3 is allowable because applied prior art doesn't describe or suggest the step of heating the semiconductor at a temperature not higher than a crystallization temperature of the semiconductor while applying the electromagnetic energy" (pages 3-4, <u>Id.</u>). In response and in accordance with the statement of allowed subject matter, independent claims 1, 8 and 13 have been amended to recite heating the semiconductor at a temperature not higher than a

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crystallization temperature of said semiconductor while applying the electromagnetic energy. Therefore, independent claims 1, 8 and 13, as amended, recite allowable subject matter, and the above-referenced rejections are believed to be moot.

Paragraph 7 of the Official Action rejects claims 4, 5 and 8-18 under the doctrine of obviousness-type double patenting over claims 1-23 of U.S. Patent No. 6,358,784 to Zhang et al. Paragraph 8 of the Official Action rejects claims 1-18 under the doctrine of obviousness-type double patenting over claims 1-24 of U.S. Patent No. 5,424,244 to Zhang et al. In response to this rejection, a *Terminal Disclaimer* will be filed as soon as it is complete. Upon filing of this *Terminal Disclaimer*, the claims of the present application are believed to be in condition for allowance. Reconsideration and withdrawal of the obviousness-type double patenting rejections are requested.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number listed below.

Respectfully submitted,

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